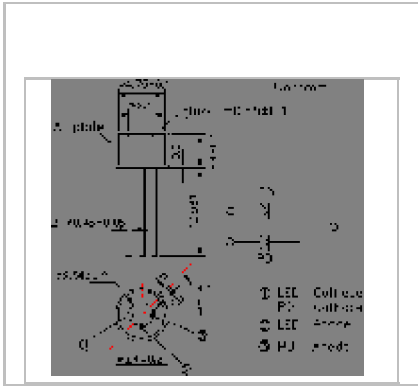


LN850/PD010-40D52 metal can sealed PD monitoring high power LED

LN850/PD010-40D52 consists of a GaAlAs LED 850nm and a Si-PD mounted on TO-18 stem hermetically sealed with a glass flat can, and is designed to monitor reflected light through detector for controlling its own output power.

†Specifications

1)Product No.	LED Lamp with PD Monitor	Outer Dimension
2)type No.	LN850/PD010-40D52	
3)Chip		
(1)material	GaAlAs Si (PIN)	
(2)Peak wavelength	850nm	
4)Package		
(1)type	TO-18	
(2)Lens	Ø2.4 Flat Glass	
(3)Cap	Metal Can (Gold Plate)	

†Absolute Maximum Ratings (Ta=25 °C)

Device	Item	Symbol	Maximum Rated Value	Unit
LED	Power Dissipation	PD	160	mW
LED	Forward Current	IF	100	mA
LED	Pulse Forward Current	IFP	1	A
LED	Reverse Voltage	VR	5	V
PD	Reverse Voltage	VR	100	V
	Operating Temperature	TOPR	-30~+85	°C
	Storage Temperature	TSTG	-30~+100	°C
	Soldering Temperature	TSOL	260	°C

Pulse Forward Current condition : duty=1% t_w =10 μ s

Soldering condition : Soldering condition must be completed within 2 seconds at 240°C

†Electro-Optical Characteristics (Ta=25 °C)

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA		1.50	1.70	V
Reverse Current	IR	VR=5V			10	μ A
Total Radiated Power	Po	IF=50mA	3.0	6.0		mW
Radiant Intensity	IE	IF=50mA	2.5	5.0		mW/sr
Peak Wavelength		IF=50mA	840	850	860	nm
Half Width		IF=50mA		35		nm
Viewing Half Angle		IF=50mA		±55		deg.
Rise Time	Tr	IF=50mA		60		ns
Fall Time	Tf	IF=50mA		40		ns
Output Current	IL	VR=0V	130	270		μ A
Dark Current	ID	VR=10V			10	nA

‡Radiant Intensity is measured by Tektronix J-6512.

‡Total Radiated Power is measured by Photodyne#500.

EPITEX INC.: 4, Nishiaketa-cho, Higashi-Kujyo, Minami-Ku, Kyoto, Japan

Tel:++81-75-682-2338 Fax:++81-75-682-2267

e-mail: sales-dep@epitex.com <http://www.epitex.com>